CMOS Micro-Power Comparator plus Voltage Follower

The MC14578 is an analog building block consisting of a very-high input impedance comparator. The voltage follower allows monitoring the noninverting input of the comparator without loading.

Four enhancement-mode MOSFETs are also included on chip. These FETs can be externally configured as open-drain or totem-pole outputs. The drains have on-chip static-protecting diodes. Therefore, the output voltage must be maintained between $V_{\rm SS}$ and $V_{\rm DD}$.

The chip requires one external component. A 3.9 M Ω ±10% resistor must be connected from the R_{bias} pin to V_{DD}. This circuit is designed to operate in smoke detector systems that comply with UL217 and UL268 specifications.

Features

Applications:

Pulse Shapers Line-Powered Smoke Detectors
Threshold Detectors Liquid/Moisture Sensors

Low-Battery Detectors

CO Detector and Micro Interface

Operating Voltage Range: 3.5 to 14 V

Operating Temperature Range: -30° to 70°C

Input Current (IN + Pin): ±1 pA @ 25°C (DIP Only)

Quiescent Current: 10 μA @ 25°C

Electrostatic Discharge (ESD) Protection Circuitry on All Pins

ORDERING INFORMATION				
Device Temperature Range		Case No.	Package	
MC14578P	-30° to 70°C	648-08	Plastic Dip	

MC14578

CMOS MICRO-POWER COMPARATOR PLUS VOLTAGE FOLLOWER



P SUFFIX PLASTIC DIP CASE 648-08

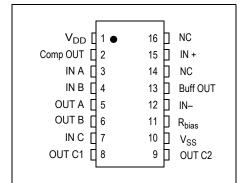


Figure 1. Pin Connections



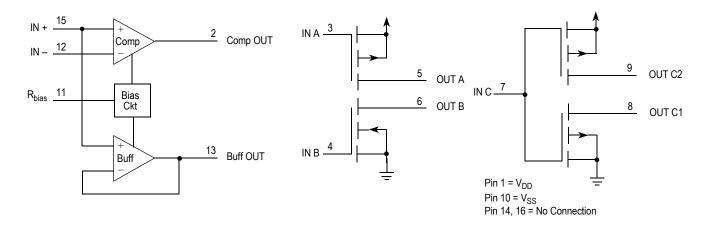


Figure 2. Block Diagram

Table 1. Maximum Ratings⁽¹⁾ (Voltages Referenced to V_{SS})

Rating	Symbol	Value	Unit
DC Supply Voltage	V_{DD}	-0.5 to +14	V
DC Input Voltage	V _{in}	-0.5 to V _{DD} +0.5	V
DC Output Voltage	V _{out}	-0.5 to V _{DD} +0.5	V
DC Input Current, Except IN +	l _{in}	±10	mA
DC Output Current, IN +	l _{in}	±1.0	mA
DC Output Current, per Pin	l _{out}	±25	mA
DC Supply Current, V _{DD} and V _{SS} Pins	I _{DD}	±50	mA
Power Dissipation, per Package	P _D	500	mW
Storage Temperature	T _{stg}	-65 to + 150	°C
Lead Temperature (10-Second Soldering)	T _L	260	°C

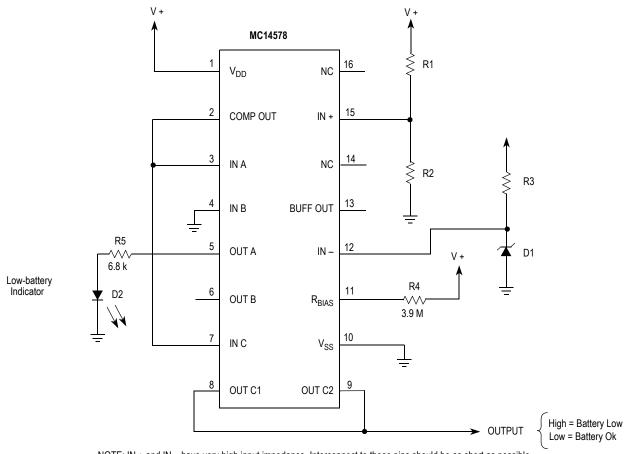
Maximum Ratings are those values beyond which damage to the device may occur. This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range V_{SS} ≤ (V_{in} or V_{out}) ≤ V_{DD}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

Table 2. Electrical Characteristics

(Voltages Referenced to V_{SS}, R_{bias} = 3.9 M Ω to V_{DD}, T_A = -30 $^{\circ}$ to 70 $^{\circ}$ C Unless Otherwise Indicated)

Characteristic	Symbol	Test Condition	V _{DD} V _{DC}	Guaranteed Limit	Unit	
Power Supply Voltage Range	V_{DD}		_	3.5 to 14.0	V	
Maximum Low-Level Input Voltage, MOSFETs Wired as Inverters; i.e., IN A tied to IN B, OUT A to OUT B, OUT C1 to OUT C2	V _{IL}	V _{out} = 9.0 V, II _{out} I <1 μA	10.0	2.0	V	
Minimum High-Level Input voltage, MOSFETs Wired as Inverters; i.e., IN A tied to IN B, OUT A to OUT B, OUT C1 to OUT C2	V _{IH}	V _{out} = 1.0 V, II _{out} I <1 μA	10.0	8.0	V	
Comparator Input Offset Voltage	V _{IO}	T _A = 25°C, Over Common Mode Range	10.0	±50	mV	
		T _A = 0° to 50°C, Over Common Mode Range	3.5 to 14.0	±75		
Comparator Common Mode Voltage Range	V _{CM}		3.5 to 14.0	0.7 to V _{DD} – 1.5	V	
Maximum Low-Level Comparator Output Voltage	V _{OL}	$\begin{aligned} &\text{IN +: V}_{\text{in}} = \text{V}_{\text{SS}}, &\text{IN -: V}_{\text{in}} = \text{V}_{\text{DD}}, \\ &\text{I}_{\text{out}} = 30 \; \mu\text{A} \end{aligned}$	10.0	0.5	V	
Minimum High-Level Comparator Output Voltage	V _{OH}	$\begin{aligned} &\text{IN +: V}_{\text{in}} = \text{V}_{\text{DD}}, \text{IN -: V}_{\text{in}} = \text{V}_{\text{SS}}, \\ &\text{I}_{\text{out}} = \text{-30 } \mu\text{A} \end{aligned}$	10.0	9.5	V	
Buffer Amp Output Offset Voltage	V ₀₀	R_{load} = 10 M Ω to V_{DD} or V_{SS} , Over Common Mode Range	_	±100	mV	
Maximum Low-Level Input Voltage, MOSFETs	V _{OL}	OUT C1, OUT C2, I _{out} = 1.1 mA	10.0	0.5	V	
Wired as Inverters; i.e., IN A tied to IN B, OUT A to OUT B, OUT C1 to OUT C2		OUT A, OUT B, I _{out} = 270 μA	10.0	0.5	V	
Minimum High-Level Input Voltage, MOSFETs	V _{OH}	OUT C1, OUT C2, I _{out} = -1.1 mA	10.0	9.5	V	
Wired as Inverters; i.e., IN A tied to IN B, OUT A to OUT B, OUT C1 to OUT C2		OUT A, OUT B, I _{out} = 270 μA	10.0	9.5	V	
Maximum Input Leakage IN + (DIP Only) Current	l _{in}	T _A = 25°C, 40% R.H., V _{in} = V _{SS} or V _{DD}	10.0	±1.0	рА	
IN + (DIP Only)		T _A = 50°C, V _{in} = V _{SS} or V _{DD}	10.0	±6.0		
IN + (SOG), IN A, IN B, IN C, IN -		$V_{in} = V_{SS}$ or V_{DD}	10.0	±40	nA	
Maximum Off-State MOSFET Leakage Current	I _{OZ}	IN A, IN C: $V_{in} = V_{DD}$, OUT A, OUT C2: $V_{out} = V_{SS}$ or V_{DD}	10.0	±100	nA	
		IN B, IN C: V _{in} = V _{SS} , OUT B, OUT C1: V _{out} = V _{SS} or V _{DD}	10.0	±100		
Maximum Quiescent Current	I _{DD}	$\begin{split} T_A &= 25^{\circ}C\\ \text{IN A, IN B, IN C: V}_{\text{in}} &= \text{V}_{\text{SS}} \text{ or V}_{\text{DD}},\\ \text{IV}_{\text{IN}} &+ -\text{V}_{\text{IN}} - \text{I} = 100 \text{ mV}\\ \text{I}_{\text{out}} &= 0 \mu\text{A} \end{split}$	10.0	10	μА	
Maximum Input Capacitance IN + Other Inputs	C _{in}	f = 1 kHz	_ _	5.0 15	pF	

APPLICATIONS INFORMATION



NOTE: IN + and IN - have very high input impedance. Interconnect to these pins should be as short as possible.

Figure 3. Low-Battery Detector

EXAMPLE VALUES

Near the switchpoint, the comparator output in the circuit of Figure 3. may chatter or oscillate. This oscillation appears on the signal labelled OUTPUT. In some cases, the oscillation in the transition region will not cause problems. For example, an MPU reading OUTPUT could sample the signal two or three times to ensure a solid level is attained. But, in a low battery detector, this probably is not necessary.

To eliminate comparator chatter, hysteresis can be added as shown in Figure 4.. The circuit of Figure 4. requires slightly more operating current than the Figure 3. arrangement.

R1	R2	R3	Nominal Tip Point
470 kΩ	1.3 MΩ	20 kΩ	4.08 V
820 kΩ	1.2 MΩ	39 kΩ	5.05 V
1.2 MΩ	1.2 MΩ	62 kΩ	6.00 V

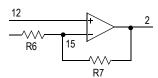
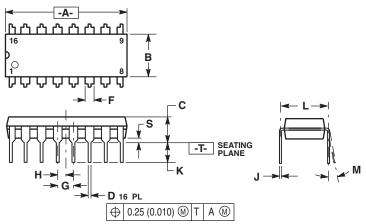
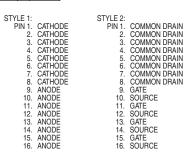


Figure 4. Adding Hysteresis

PACKAGE DIMENSIONS





CASE 648-08 ISSUE R 16-LEAD PLASTIC DIP

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	ETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100 BSC		2.54 BSC		
Н	0.050 BSC		1.27 BSC		
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
M	0	10	0	10	
S	0.020	0.040	0.51	1.01	

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